

# Citations for Target : **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1964</b>	Pohlan, C. Lutz, H. Sizmann, R. 'Uberreichweiten Schneller Ionen in Diamantstrukturen' <i>Z. Angew. Phys.</i> , <b>17</b> , 404-06 (1964) <i>Comment</i> : R, dR. 80 keV Kr -> GaAs (Cryst.)	<b>1964-Pohl</b> 0188
<b>1968</b>	Sattler, A. R. Dearnaley, G. 'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si' <i>Phys. Rev.</i> , <b>161</b> , 244-52 (1967)(Erratum, <i>Phys. Rev.</i> , <b>165</b> , 750 (1968)) <i>Comment</i> : S. 4-7.6 MeV H, D -> Ge, GaAs, Si (All Cryst.)	<b>1968-Satt</b> 0308
<b>1968</b>	Sattler, A. R. Vook, F. L. 'Channeling in Zinc-Blende Lattices: Energy-Loss Studies for Hydrogen and Helium Ions in InAs, GaSb, AlSb, and InSb' <i>Phys. Rev.</i> , <b>175</b> , 526-32 (1968) <i>Comment</i> : S. (2-8 MeV) H, D, He, -> InAs, GaSb, InSb, AlSb (All (Cryst.)	<b>1968-Satt2</b> 0601
<b>1969</b>	Narayanan, G. H. Spitzer, W. G. 'The Structural Characteristics of Radiation Damage Produced by High Energy (2.7 MeV) Ion Implantation in GaAs' <i>J. Matl. Sci.</i> , <b>13</b> , 2418-2428 (1978) <i>Comment</i> : R, dR. N, P (2.7 MeV) -> GaAs	<b>1969-Nara</b> 2125
<b>1969</b>	Whitton, J. L. Carter, G. Freeman, J. H. Gard, G. A. 'The Implantation Profiles of 10, 20 and 40 keV 95Kr in Gallium Arsenide' <i>J. Mat. Sci.</i> , <b>4</b> , 208-17 (1969) <i>Comment</i> : R, dR. 10-40 keV Kr -> GaAs	<b>1969-Whit2</b> 0378
<b>1970</b>	Whitton, J. L. Carter, G. 'The Implantation Profiles of Energetic Heavy Ions in GaAs, GaP, and Ge' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, 615-32 (1970)</i> <i>Comment</i> : R, dR. 10-40 keV S, Kr, Na -> GaAs,	<b>1970-Whit</b> 0022
<b>1971</b>	Whitton, J. L. Bellavance, G. R. 'Ion Implantation of Sulphur into GaAs, GaP and Ge Monocrystals' <i>Rad. Effects</i> , <b>9</b> , 127-31 (1971) <i>Comment</i> : R, dR. 20-40 keV S -> GaAs (Cryst. Axial And Random)	<b>1971-Whit</b> 0681
<b>1972</b>	Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: II: Range Distributions Derived from Collection and Sputter-Etch Curves.' <i>Rad. Effects</i> , <b>16</b> , 107-114 (1972) <i>Comment</i> : R. 10-30 keV Kr, Tl -> GaAs, GaP, Ge, Si	<b>1972-Cart</b> 0976

# Citations for Target : **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1972</b>	Harris, J. S. Harris, J. M. Marcus, H. L. 'Fluorine Ion Implantation Profiles in Gallium Arsenide as Determined by Auger Electron Spectroscopy' <i>Appl. Phys. Letters, 21, 598-600 (1972)</i> <i>Comment : R. 30 keV F -&gt; GaAs</i>	<b>1972-Harr</b> 0997
<b>1972</b>	Mamontov, A. P. Okunev, V. D. Gaman, V. I. Zakharov, B. G. 'Distribution of Radiation Defects in Gallium Arsenide Irradiated with Deuterons' <i>Sov. Phys. Semicond., 6, 747-749 (1972)</i> <i>Comment : R. 4-12 keV D -&gt; GaAs</i>	<b>1972-Mamo</b> 0998
<b>1972</b>	Whitton, J. L. Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: I Saturation Effects.' <i>Rad. Effects, 16, 101-105 (1972)</i> <i>Comment : R, dR. 10-30 keV Kr, Tl -&gt; Si, Ge, GaP, GaAs</i>	<b>1972-Whit</b> 0975
<b>1974</b>	Langley, R. A. 'Range-Energy Relations for C Ions and O Ions in N <sub>2</sub> , O <sub>2</sub> , and Tissue-Equivalent Gas' <i>Phys. Med. Biol., 19, 495-503 (1974)</i> <i>Comment : R, dR. (0.3-2.5 MeV) C, (0.5-5.0 MeV) O -&gt; N<sub>2</sub>, O<sub>2</sub>, Tissue-Equivalent Gas</i>	<b>1974-Lang</b> 1276
<b>1975</b>	Al-Bedri, M. B. Harris, S. J. 'Energy Straggling of Fission Fragments in Gases and Solids' <i>Nucl. Inst. Methods, 124, 125-130 (1975)</i> <i>Comment : dS. Cf Fiss. Frag. -&gt; He, N, CO<sub>2</sub>, Ar, Kr, Ne, Air, Al, Ag, Cu, Au, CH<sub>4</sub>, Tissue Eq. Gas</i>	<b>1975-Al</b> 1273
<b>1975</b>	Ambridge, T. Heckingbottom, R. 'Effect of Dual Implants into GaAs' <i>Elec. Letters, 11 (1975)</i> <i>Comment : R. 350 keV Se, Ga -&gt; GaAs</i>	<b>1975-Ambr</b> 0957
<b>1975</b>	Lyons, R. P. Ehret, . E. Park, Y. S. 'Ion Implantation of Diatomic Sulphur into GaAs' <i>Bull. Am. Phys. Soc., 20, 318 (1975)</i> <i>Comment : R. About 100 keV S<sub>2</sub> -&gt; GaAs.</i>	<b>1975-Lyon</b> 0530
<b>1976</b>	Comas, J. Plew, L. 'Beryllium and Sulfur Ion-Implanted Profiles in GaAs' <i>J. Elec. Mater., 5, 209-221 (1976)</i> <i>Comment : R. 100, 200 keV Be, S -&gt; GaAs</i>	<b>1976-Coma</b> 1021

# Citations for Target : **As**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1976</b>	Comas, J. Plew, L. Chatterjee, P. K. Mclevige, W. V. Vaidyanathan, K. V. 'Impurity Distribution of Ion-Implanted Be in GaAs by Sims, Photoluminescence, and Electrical Profiling' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 141-148 (1976)</i> <i>Comment : R. 250 keV Be -&gt; GaAs</i>	<b>1976-Coma2</b> 1066
<b>1976</b>	Dietrich, H. B. Comas, J. 'Anomalous Redistribution of Ion-Implanted Dopants' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 735-742 (1976)</i> <i>Comment : R. 60 keV Al -&gt; Si, 100 keV Be -&gt; Si, GaAs</i>	<b>1976-Diet</b> 1069
<b>1976</b>	Eisen, F. H. Welch, B. M. 'Radiotracer Profiles in Sulfur Implanted GaAs' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 97-106 (1976)</i> <i>Comment : R. 100 keV 35S -&gt; GaAs</i>	<b>1976-Eise</b> 1065
<b>1976</b>	Harris, T. J. Sealy, B. J. SurrIDGE, R. K. 'Effects of Channelling on the Electrical Properties of Donor Implanted GaAs' <i>Elec. Letters, 12, 664-665 (1976)</i> <i>Comment : R. 90 keV Sn, 90-300 keV Te -&gt; GaAs</i>	<b>1976-Harr</b> 0958
<b>1976</b>	Kachare, A. H. Spitzer, W. G. Fredrickson, J. E. Euler, F. K. 'Measurements of Layer Thicknesses and Refractive Indices in High Energy Ion Implanted GaAs and GaP' <i>J. Appl. Phys., 47, 5347-5381 (1976)</i> <i>Comment : R. N, P (3 MeV) -&gt; GaAs, GaP</i>	<b>1976-Kach</b> 2149
<b>1976</b>	Neuwirth, W. Pietsch, W. Hauser, U. 'Stopping Cross Sections of Elements with Z=2 to 87 for Li Ions with Energies Between 80 keV and 840 keV' <i>Physics Data, Erstes Physikalisches Institut, Univ. Zu Koln, Germany (1976)</i> <i>Comment : S. 80-840 keV Li -&gt; (2 &lt;= Z2 &lt;= 87)</i>	<b>1976-Neuw</b> 1178
<b>1977</b>	Lee, D. H. Malbon, R. M. 'Ion-Implanted Silicon Profiles in GaAs' <i>Appl. Phys. Letters, 30, 327-329 (1977)</i> <i>Comment : R, dR. 50-500 keV Si -&gt; GaAs</i>	<b>1977-Lee</b> 1026
<b>1977</b>	Matsumura, H. Nagatomo, M. Furukawa, S. 'Range of Protons in GaAs' <i>Rad. Effects, 33, 121-123 (1977)</i> <i>Comment : R. 300-500 keV H -&gt; GaAs</i>	<b>1977-Mats</b> 0967

# Citations for Target : **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1977</b>	Matsumura, H. Stephens, K. G. 'Electrical Measurement of the Lateral Spread of the Proton Isolation Layer in GaAs' <i>J. Appl. Phys.</i> , <b>48</b> , 2779-83 (1977). <i>Comment</i> : R, dR, R(Lateral). 300-500 keV H -> GaAs (Conc. Determined By Carrier Removal).	<b>1977-Mats2</b> 0935
<b>1977</b>	Molnar, B. Kennedy, T. A. 'GaAs Ion-Implantation Parameters Studied through Contactless Mobility Measurements' <i>Electrochem. Soc. Extended Abstracts</i> , 261-262, May (1977) <i>Comment</i> : R. 120 keV S -> GaAs	<b>1977-Moln</b> 1059
<b>1977</b>	Surridge, R. K. Sealy, B. J. 'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs' <i>Appl. Phys.</i> , <b>10</b> , 911-917 (1977) <i>Comment</i> : R. 200 And 300 keV Sn, Ge, Se, Te -> GaAs	<b>1977-Surr</b> 0955
<b>1977</b>	Surridge, R. K. Sealy, B. J. D'Cruz, A. D. E. Stephens, K. G. 'Annealing Kinetics of Donor Ions Implanted into GaAs' <i>Gallium Arsenide and Related Compounds (Edinburgh)</i> , Ed. by C. Hilsum, 161-167 (1977) <i>Comment</i> : R. 200 keV Se, Sn -> GaAs	<b>1977-Surr2</b> 0956
<b>1977</b>	Surridge, R. K. Sealy, B. J. 'Active Layers for Device Applications by using High-Energy Selenium Implantation into GaAs' <i>Elec. Letters</i> , <b>13</b> , 233-234 (1977) <i>Comment</i> : R. 150 keV Sn, 1 MeV Se -> GaAs	<b>1977-Surr3</b> 0959
<b>1978</b>	Anderson, W. J. Park, Y. S. 'Flux and Fluence Dependence of Implantation Disorder in GaAs Substrates' <i>J. Appl. Phys.</i> , <b>49</b> , 4568-4570 (1978) <i>Comment</i> : R, dR. 100 keV Ne, Ar, Kr -> GaAs	<b>1978-Ande3</b> 1216
<b>1978</b>	Golovchenko, J. A. Venkatesan, T. N. C. 'Annealing of Te-Implanted GaAs by Ruby Laser Irradiation' <i>Appl. Phys. Letters</i> , <b>32</b> , 147-149 (1978) <i>Comment</i> : R. 50 keV Te -> GaAs	<b>1978-Golo</b> 1099
<b>1978</b>	Lidow, A. Gibbons, J. F. Deline, V. R. Evans, C. A. 'Fast Diffusion of Elevated-Temperature Ion-Implanted Se in GaAs as Measured by Secondary Ion Mass Spectrometry' <i>Appl. Phys. Letters</i> , <b>32</b> , 149-151 (1978) <i>Comment</i> : R. 120, 150 keV Se -> As	<b>1978-Lido</b> 1100

# Citations for Target : **As**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1978</b>	Matthias, D. Samuel, B. Ann, T. 'Radiation Damage to Tissue Equivalent Gas from MeV Heavy Ions' <i>Biol. Res. Methods, A0, 26-34 (1978)</i> <i>Comment : S. R. He, C, N, O (1-10 MeV) -&gt; Tiss. Eq. Gas</i>	<b>1978-Matt2</b> 2411
<b>1978</b>	Muller, G. Haubold, M. Schimko, R. Trapp, M. Schwarz, G. 'Investigations on the Diffusion of Implanted Zinc in GaAs(1-X)P(X) by Ion Microprobe' <i>Phys. Stat. Sol. A, 49, 279-284 (1978)</i> <i>Comment : R. 100 keV Zn -&gt; GaAsP</i>	<b>1978-Mull</b> 1239
<b>1978</b>	Rao, E. V. K. Duhamel, N. Favennec, P. N. L'Haridon, H. 'Investigation of Compensation in Implanted N-GaAs' <i>J. Appl. Phys., 49, 3898-3905 (1978)</i> <i>Comment : R, dR. 200 keV-1 MeV H, B, As -&gt; GaAs</i>	<b>1978-Rao</b> 1215
<b>1978</b>	Shin, B. K. Ehret, J. E. Park, Y. S. Stefiniw, M. 'Dual Implantation of C+ and Ga+ Ions into GaAs' <i>J. Appl. Phys., 49, 2988-2990 (1978)</i> <i>Comment : R. 120 keV Ga, 60 keV C -&gt; GaAs</i>	<b>1978-Shin</b> 1112
<b>1978</b>	Vedmanov, G. D. Neshov, F. G. Puzanov, A. A. Urmanov, A. R. 'Determining Stopping Power from Spectra of Backscattered Ions' <i>Sov. Atom. Energy, 45, 989-991 (1978)</i> <i>Comment : S. N (0.75-7.4MeV) -&gt; Fe, Ge, GaAs, FeGe2</i>	<b>1978-Vedm</b> 1537
<b>1979</b>	Inada, T. Kato, S. Maeda, Y. Tokunaga, K. 'Doping Profiles in Zn-Implanted GaAs after Laser Annealing' <i>J. Appl. Phys., 50, 6000-6002 (1979)</i> <i>Comment : R, dR. 100 keV Zn -&gt; GaAs</i>	<b>1979-Inad</b> 1297
<b>1979</b>	Kang, S. T. Shimizu, R. Okutani, T. 'Sputtering of Si with keV Ar+ Ions. II. Computer Simulation of Sputter Broadening Due to Ion Bombardment in Depth Profiling.' <i>Jap. J. Appl. Phys., 18, 1987-1994 (1979)</i> <i>Comment : R, dR. 45 keV As -&gt; GaAs</i>	<b>1979-Kang</b> 1337
<b>1979</b>	Kasahara, J. Arai, M. Watanabe, N. 'Suppression of Thermal Conversion in Cr-Doped Semi-Insulating GaAs' <i>J. Appl. Phys., 50, 8229-8231 (1979)</i> <i>Comment : R, dR. 70-130 keV Si -&gt; GaAs</i>	<b>1979-Kasa</b> 1300
<b>1979</b>	Muller, G. Trapp, M. Schimko, R. Richter, C. E. 'Measurement of Range Distributions of Zinc and Nitrogen Ions in Multiple-Layer Substrates with Secondary Ion Microprobe' <i>Phys. Stat. Sol. A, 51, 87-92 (1979)</i> <i>Comment : R, dR. 50-300 keV N, Zn -&gt; SiO2-GaAs(1-X)P(X), SiO2-Si3N4</i>	<b>1979-Mull</b> 1237

# Citations for Target : **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1979</b>	Park, Y. S. Grant, J. T. Haas, T. W. 'The Determination of Sulfur-Ion-Implantation Profiles in GaAs using Auger Electron Spectroscopy' <i>J. Appl. Phys.</i> , 50, 809-812 (1979) <i>Comment</i> : R, dR. 60, 120 keV S+, S2+ -> GaAs	<b>1979-Park</b> 1221
<b>1979</b>	Tandon, J. L. Nicolet, M-A. Eisen, F. H. 'Silicon Implantation in GaAs' <i>Appl. Phys. Letters</i> , 34, 165-167 (1979) <i>Comment</i> : R, dR. 300 keV Si -> GaAs	<b>1979-Tand</b> 1207
<b>1979</b>	Williamson, K. R. Theis, W. M. Yun, S. S. Park, Y. S. Ehret, J. E. 'Glow-Discharge Optical Spectroscopy Measurement of B-, Ge-, and Mg-Implanted GaAs' <i>J. Appl. Phys.</i> , 50, 8019-8024 (1979) <i>Comment</i> : R, dR. 60-120 keV B, Ge, Mg -> GaAs	<b>1979-Will</b> 1304
<b>1979</b>	Yeo, Y. K. Park, Y. S. Yu, P. W. 'Electrical Measurements and Optical Activation Studies in Mg-Implanted GaAs' <i>J. Appl. Phys.</i> , 50, 3274-3281 (1979) <i>Comment</i> : R, dR. 120 keV Mg -> GaAs (Cr-Doped)	<b>1979-Yeo</b> 1225
<b>1980</b>	Tashlykov, I. S. 'Backscattering Measurements of P+ Implanted GaAs Crystals' <i>Nucl. Inst. Methods</i> , 170, 403-406 (1980) <i>Comment</i> : R, dR. 30-60 keV P -> GaAs	<b>1980-Tash</b> 1379
<b>1983</b>	Wilson, R. G. Jamba, D. M. Deline, V. R. Evans, C. A. Park, Y. S. 'Depth Distributions of Sulfur Implanted into GaAs as a Function of Ion Energy, Ion Fluence, and Annealing Temperature and Encapsulation' <i>J. Appl. Phys.</i> , 54, 3849-3854 (1983) <i>Comment</i> : R. S (40-600 keV) -> GaAs	<b>1983-Wils</b> 2023
<b>1991</b>	Arstila, K. Keinonen, J. Tikkanen, P. 'Stopping Power for Low-Velocity Mg Ions in Si, Ge and GaAs' <i>Phys. Rev. B</i> , 43, 13967-13970 (1991) <i>Comment</i> : S. Mg (0-0.8 MeV/amu) -> Si, Ge, GaAs	<b>1991-Arst</b> 1910
<b>1994</b>	Kido, Y. Ikeda, A. Yamamoto, Y. Nakata, J. Yamaguchi, H. 'Impact Parameter Dependent Stopping Powers for Axially Channeled and Semi-Channeled MeV He Ions in GaAs:Er' <i>Phys. Rev. B</i> , 49, 14387-14396 (1994) <i>Comment</i> : S. He (2 MeV) -> GaAs Channeling Effects	<b>1994-Kido</b> 2044
<b>1994</b>	Raisanen, J. Rauhala, E. 'Ranges of 1.0-2.7 MeV H and He Ions in GaAs' <i>Nucl. Inst. Methods</i> , B93, 1-4 (1994) <i>Comment</i> : R. H, He (1.0-2.7 MeV) -> GaAs	<b>1994-Rais</b> 1129

# Citations for Target : **As**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1996</b>	Misdaq, M. A. Ellassali, R. 'Average Stopping Powers for Channeled Ions using Computational and Experimental Methods' <i>Nucl. Inst. Methods, 119, 325-330 (1996)</i> <i>Comment : S. Light ions -&gt; Si, GaAs (channeled)</i>	<b>1996-Misd</b> 0964
<b>1996</b>	Rajatora, M. Vakevainen, K. Ahlgren, T. Rauhala, E. Raisanen, J. 'Stopping Powers of GaAs for 0.3-2.5 MeV H and He Ions' <i>Nucl. Inst. Methods, B119, 457-462 (1996)</i> <i>Comment : S. H, He (0.3-2.5 MeV) -&gt; GaAs</i>	<b>1996-Raja</b> 2165
<b>2004</b>	Nigam, M. Duggan, J.L. Bounanani, M. El. Yang, C. Ravi, G. V. 'Stopping power of thin GaAs films for Si and P ions' <i>Nucl.Instrum.Methods B219-220, 273 (2004)</i> <i>Comment : S. Si, P (0.07 - 0.3 MeV/n) -&gt; GaAs</i>	<b>2004-Niga</b> 3213